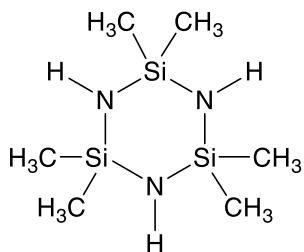


Catalog # 14-1510 2,2,4,4,6,6-Hexamethylcyclotrisilazane, 97%



Thermal Behavior:

- Melting point: -10°C
- Boiling point: 186-188 °C

Technical Notes:

1. Precursor used for thin silicon film deposition.

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
SiC _x N _y	PE-CVD PE-CVD	Plasma Plasma	10 ⁻² -10 Torr -	He N ₂ , He, NH ₃	100-1027°C 100-750°C	1 2
Fe: SiC _x N _y	CVD	-	-	Cp ₂ Fe, He	900-1000°C	3

References:

1. [Glass Phys. Chem. 2009, 35, 274.](#)
2. [Thin Solid Films, 2012, 520, 5906.](#)
3. [J. Magn. Magn. Mater. 2020, 499, 166242.](#)